

### **Features**

- Very Low FOM R<sub>DS(on)</sub> × Q<sub>g</sub>
- Epoxy Meets UL 94 V-0 Flammability Rating
- · Halogen Free Available Upon Request By Adding Suffix "-HF"
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

# **Maximum Ratings**

Operating Junction Temperature Range : -55°C to +150°C

Storage Temperature Range: -55°C to +150°C

Thermal Resistance: 80°C/W Junction to Ambient

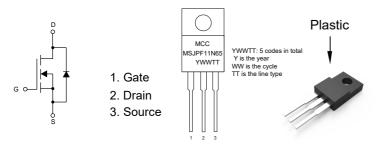
• Thermal Resistance: 4°C/W Junction to Case

Parameter	Symbol	Rating	Unit	
Drain-Source Voltage	V <sub>DS</sub>	650	V	
Gate-Source Volltage	V <sub>GS</sub>	±30	V	
Continuous Drain Current	I <sub>D</sub>	11	Α	
Pulsed Drain Current (Note 1	I <sub>DM</sub>	33	Α	
Single Pulse Avalanche Er	E <sub>AS</sub>	211	mJ	
Avalanche Current (Note 1)	I <sub>AR</sub>	1.6	Α	
Repetitive Avalanche Energy (Note 1)		E <sub>AR</sub> 0.32		mJ
Total Power Dissipation	T <sub>C</sub> =25°C	P <sub>D</sub>	31.3	W

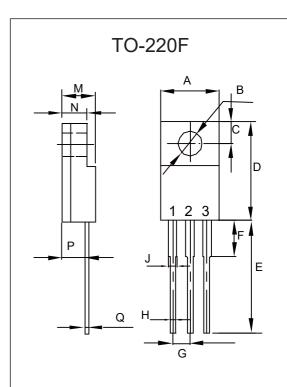
Note: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.

2.  $I_{AS}$ =1.6A,  $V_{DD}$ =50V,  $R_{G}$ =25 $\Omega$ , Starting  $T_{J}$ =25 $^{\circ}C$  .

# **Internal Structure and Marking Code**



# N-CHANNEL Super-Junction Power MOSFET



DIMENSIONS					
DIM INCHES		MM		NOTE	
DIIVI	MIN	MAX	MIN	MAX	NOTE
Α	0.392	0.421	9.96	10.70	
В	0.138		3.50		Ф
С	0.106		2.70		TYP.
D	0.567	0.642	14.40	16.30	
Е	0.520		13.20		TYP.
F		0.177		4.50	
G	0.100		2.54		TYP.
Н	0.020	0.035	0.50	0.90	
J	0.043	0.053	1.10	1.35	
M	0.169	0.201	4.30	5.10	
N		0.140		3.56	
Р	0.083	0.126	2.10	3.20	
Q	0.020	0.032	0.50	0.80	



# Electrical Characteristics @ 25°C (Unless Otherwise Specified)

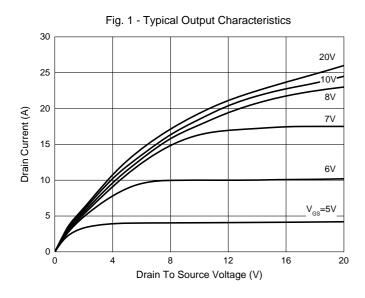
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	650			V
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±30V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =650V, V <sub>GS</sub> =0V			1	μA
		V <sub>DS</sub> =650V, V <sub>GS</sub> =0V, T <sub>J</sub> =150°C			100	
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_D=250\mu A$	2.5		4	V
Drain-Source On-Resistance (Note 3)	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =5.5A		0.34	0.38	Ω
Forward tranconductance (Note 3)	<b>g</b> <sub>FS</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =5.5A		7.8		S
Dynamic Characteristics(Note 4)			'			
Input Capacitance	C <sub>iss</sub>			901		pF
Output Capacitance	C <sub>oss</sub>	$V_{DS}$ =50V, $V_{GS}$ =0V,f=1MHz		50		
Reverse Transfer Capacitance	C <sub>rss</sub>			5.5		
Total Gate Charge	$Q_g$			21		
Gate-Source Charge	$Q_{gs}$	V <sub>DD</sub> =520V,V <sub>GS</sub> =10V,I <sub>D</sub> =11A		4.5		nC
Gate-Drain Charge	$Q_{gd}$			7		
Turn-On Delay Time	t <sub>d(on)</sub>			41		
Turn-On Rise Time	t <sub>r</sub>	$V_{DD} = 400 \text{V}, I_{D} = 11 \text{A}, R_{G} = 25 \Omega$		20		ns
Turn-Off Delay Time	t <sub>d(off)</sub>	V <sub>DD</sub> -400V, I <sub>D</sub> -11A,R <sub>G</sub> -23Ω		123		
Turn-Off Fall Time	t <sub>f</sub>			6.4		
Drain-Source Body Diode Cha	racteristi	cs				
Continuous Body Diode Current	Is	T -25°C			9.2	Λ
Pulsed Diode Forward Current	I <sub>SM</sub>	T <sub>C</sub> =25°C			29	A
Body Diode Voltage	V <sub>SD</sub>	I <sub>SD</sub> =11A, V <sub>GS</sub> =0V		0.9	1.2	V
Reverse Recovery Time	t <sub>rr</sub>			280		ns
Reverse Recovery Charge	Q <sub>rr</sub>	$V_R$ =520V, $I_F$ = $I_S$ , $di_F$ / $dt$ =100A/ $\mu$ s		2.8		μC
Peak Reverse Recovery Current	I <sub>rrm</sub>			17		Α

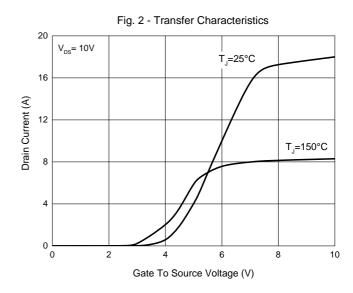
Note 3. Pulse Test : Pulse Width≤300µs, Duty Cycle ≤ 1%.

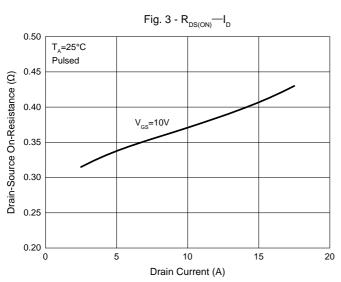
4. Guaranteed by Design, Not Subject to Production Testing.

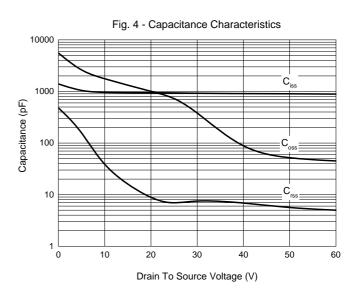


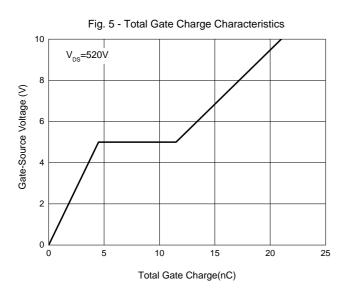
## **Curve Characteristics**

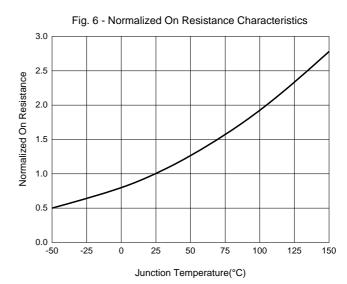




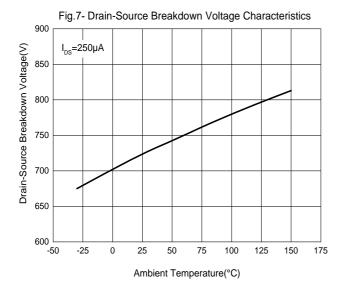


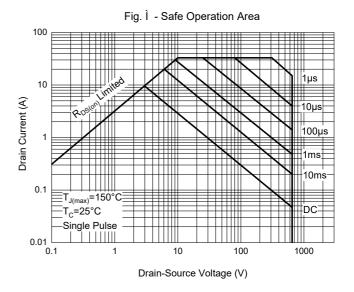












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## **Ordering Information**

Device	Packing
Part Number-BP	Bulk:50pcs/Tube,1Kpcs/Box,5Kpcs/Carton

Note: Adding "-HF" Suffix For Halogen Free, eg. Part Number-BP-HF

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